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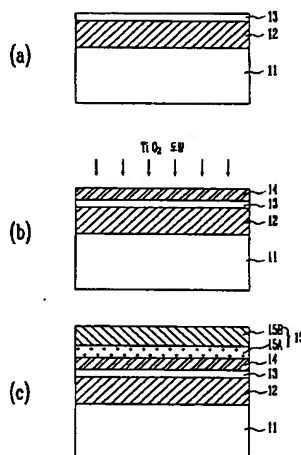
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(54) METHOD FOR MANUFACTURING CAPACITOR OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: A method for manufacturing a capacitor of a semiconductor device is provided to improve capacitance and a leakage current characteristic, by doping titanium oxide having an excellent dielectric characteristic to form a dielectric layer when tantalum oxide is deposited.

CONSTITUTION: After a lower electrode(12) is formed on a substrate(11) having a lower structure, a rapid thermal nitride layer(13) is formed on the lower electrode. Tantalum oxide is deposited on the rapid thermal nitride layer while titanium oxide is doped to form a dielectric layer(14). An upper electrode (15) is formed on the dielectric layer.



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